Freescale Semiconductor
Technical Data

Document Number: MRF5S21090H
Rev. 3, 10/2008

RoHS

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

MRF5S21090HR3
MRF5S21090HSR3

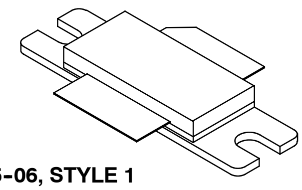
Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

- Typical 2-carrier W-CDMA Performance: V_{DD} = 28 Volts, I_{DQ} = 850 mA, P_{out} = 19 Watts Avg., f = 2112.5 MHz, Channel Bandwidth = 3.84 MHz, PAR = 8.5 dB @ 0.01% Probability on CCDF.
  - Power Gain — 14.5 dB
  - Drain Efficiency — 26%
  - IM3 @ 10 MHz Offset — -37.5 dBc in 3.84 MHz Channel Bandwidth
  - ACPR @ 5 MHz Offset — -40.5 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2140 MHz, 90 Watts CW Output Power

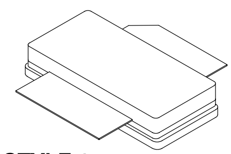
Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Low Gold Plating Thickness on Leads, 40μ″ Nominal.
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

2110-2170 MHz, 19 W AVG., 28 V
2 x W-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465-06, STYLE 1
NI-780
MRF5S21090HR3



CASE 465A-06, STYLE 1
NI-780S
MRF5S21090HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	269 1.5	W W/°C
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature	T_J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 80°C, 90 W CW Case Temperature 76°C, 19 W CW	$R_{\theta JC}$	 0.65 0.69	°C/W

1. MTTF calculator available at http://www.freescale.com/rf. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers.* Go to http://www.freescale.com/rf. Select Documentation/Application Notes - AN1955.

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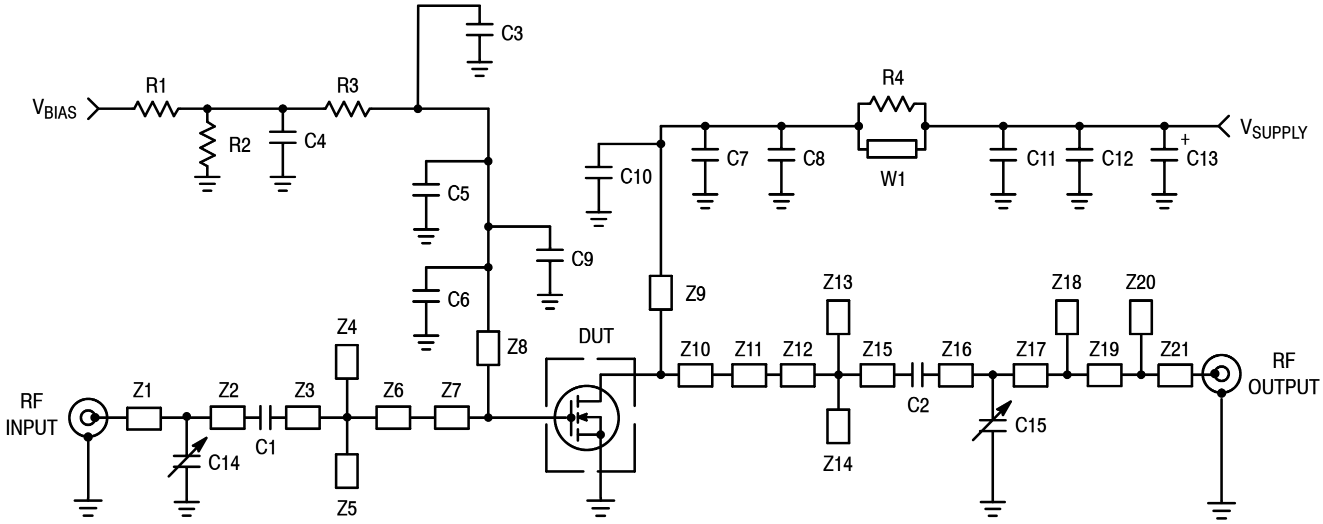
Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M3 (Minimum)
Charge Device Model	C7 (Minimum)

Table 4. Electrical Characteristics (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Zero Gate Voltage Drain Leakage Current (V_{DS} = 65 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current (V_{DS} = 28 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	1	μAdc
On Characteristics (DC)					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 200 μAdc)	$V_{GS(th)}$	2.5	2.9	3.5	Vdc
Gate Quiescent Voltage (V_{DS} = 28 Vdc, I_D = 850 mAdc)	$V_{GS(Q)}$	—	3.9	—	Vdc
Drain-Source On-Voltage (V_{GS} = 10 Vdc, I_D = 2 Adc)	$V_{DS(on)}$	—	0.25	—	Vdc
Forward Transconductance (V_{DS} = 10 Vdc, I_D = 2 Adc)	g_{fs}	—	5	—	S
Dynamic Characteristics (1)					
Reverse Transfer Capacitance (V_{DS} = 28 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{rss}	—	1.7	—	pF
Functional Tests (In Freescale Test Fixture, 50 ohm system) V_{DD} = 28 Vdc, I_{DQ} = 850 mA, P_{out} = 19 W Avg., f = 2112.5 MHz, 2-carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @ ±5 MHz Offset. IM3 measured in 3.84 MHz Bandwidth @ ±10 MHz Offset. PAR = 8.5 dB @ 0.01% Probability on CCDF.					
Power Gain	G_{ps}	12.5	14.5	—	dB
Drain Efficiency	η_D	24	26	—	%
Intermodulation Distortion	IM3	—	-37.5	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-40.5	-38	dBc
Input Return Loss	IRL	—	-15	-9	dB

1. Part is internally matched both on input and output.

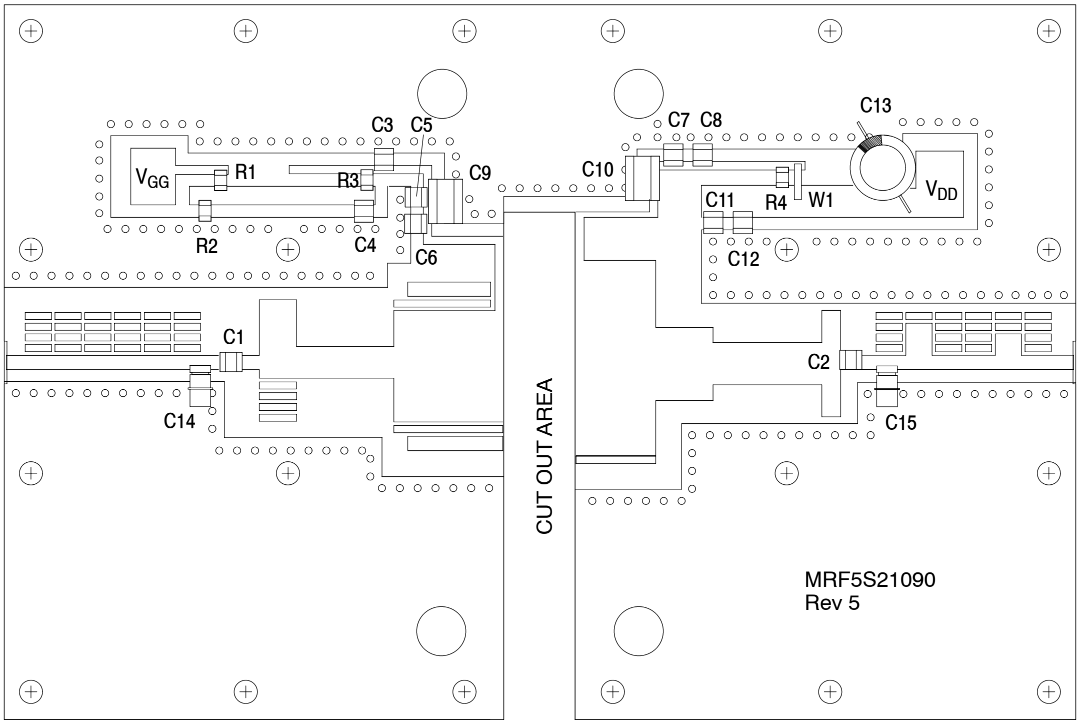


Z1	1.0856″ x 0.080″ Microstrip	Z12	0.609″ x 0.220″ Microstrip
Z2	0.130″ x 0.080″ Microstrip	Z13	0.290″ x 0.106″ Microstrip
Z3	0.230″ x 0.080″ Microstrip	Z14	0.290″ x 0.106″ Microstrip
Z4	0.347″ x 0.208″ Microstrip	Z15	0.080″ x 0.025″ Microstrip
Z5	0.090″ x 0.208″ Microstrip	Z16	1.080″ x 0.160″ Microstrip
Z6	0.650″ x 0.176″ Taper	Z17	0.180″ x 0.080″ Microstrip
Z7	0.623″ x 0.610″ Microstrip	Z18	0.260″ x 0.147″ Microstrip
Z8	0.044″ x 0.881″ Microstrip	Z19	0.500″ x 0.080″ Microstrip
Z9	0.044″ x 0.869″ Microstrip	Z20	0.199″ x 0.147″ Microstrip
Z10	1.076″ x 0.446″ Microstrip	Z21	0.365″ x 0.080″ Microstrip
Z11	0.320″ x 0.393″ Microstrip	PCB	Arlon GX0300-55-22, 0.03″, ε_r = 2.55

Figure 1. MRF5S21090HR3(HSR3) Test Circuit Schematic

Table 5. MRF5S21090HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1	9.1 pF Chip Capacitor	ATC100B9R1CT500XT	ATC
C2	8.2 pF Chip Capacitor	ATC100B8R2CT500XT	ATC
C3	2.0 pF Chip Capacitor	ATC100B2R0BT500XT	ATC
C4, C12	0.1 μF Chip Capacitors	CDR33BX104AKYS	Kemet
C5	5.6 pF Chip Capacitor	ATC100B5R6CT500XT	ATC
C6	5.1 pF Chip Capacitor	ATC100B5R1CT500XT	ATC
C7	7.5 pF Chip Capacitor	ATC100B7R5JT500XT	ATC
C8	1.2 pF Chip Capacitor	ATC100B1R2BT500XT	ATC
C9, C10	0.56 μF Chip Capacitors	700A561MT150XT	ATC
C11	1000 pF Chip Capacitor	ATC100B102JT500XT	ATC
C13	470 μF, 35 V Electrolytic Capacitor	EKME630ELL471MK25S	Nippon Chemi-Con
C14, C15	0.4 – 2.5 Variable Capacitors, Gigatrim	27281SL	Johanson
R1	1 kΩ, 1/4 W Chip Resistor	CRCW12061001FKEA	Vishay
R2	560 kΩ, 1/4 W Chip Resistor	CRCW12065600FKEA	Vishay
R3, R4	12 Ω, 1/4 W Chip Resistors	CRCW120612R0FKEA	Vishay
W1	Wire Strap		



Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/-logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. MRF5S21090HR3(HSR3) Test Circuit Component Layout

ARCHIVE INFORMATION

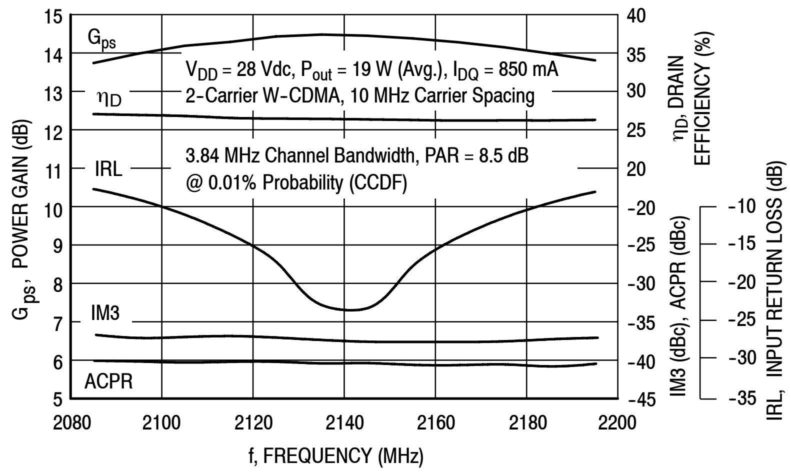


Figure 3. 2-Carrier W-CDMA Broadband Performance

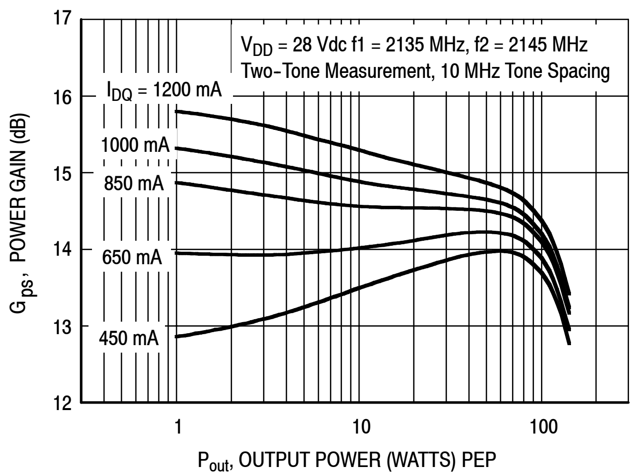


Figure 4. Two-Tone Power Gain versus Output Power

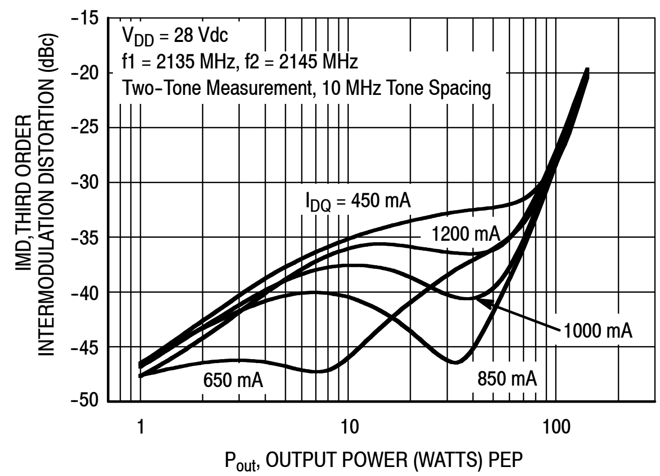


Figure 5. 3rd Order Intermodulation Distortion versus Output Power

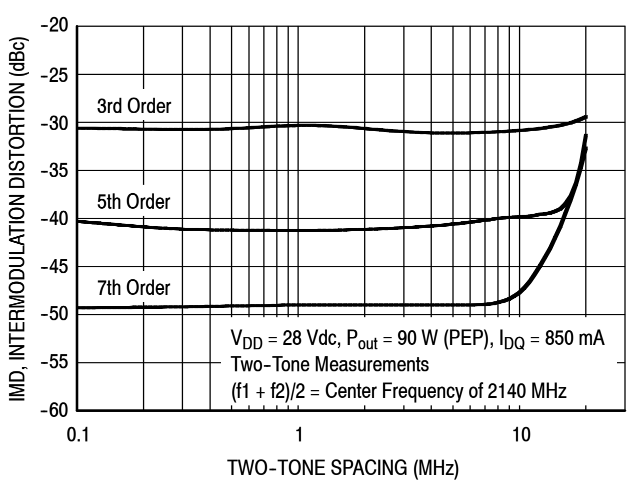


Figure 6. Intermodulation Distortion Products versus Tone Spacing

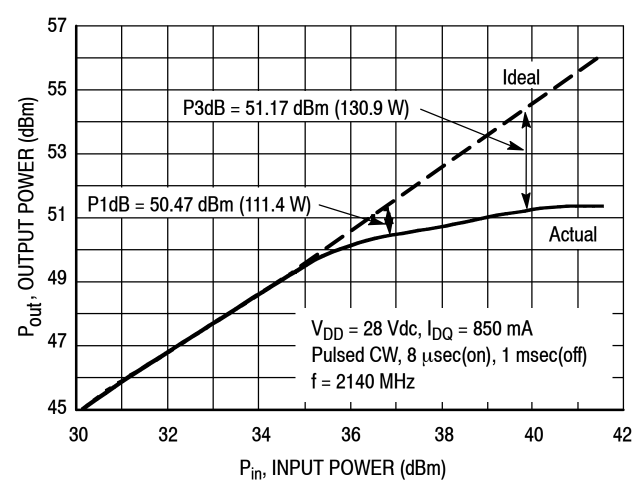


Figure 7. Pulse CW Output Power versus Input Power

TYPICAL CHARACTERISTICS

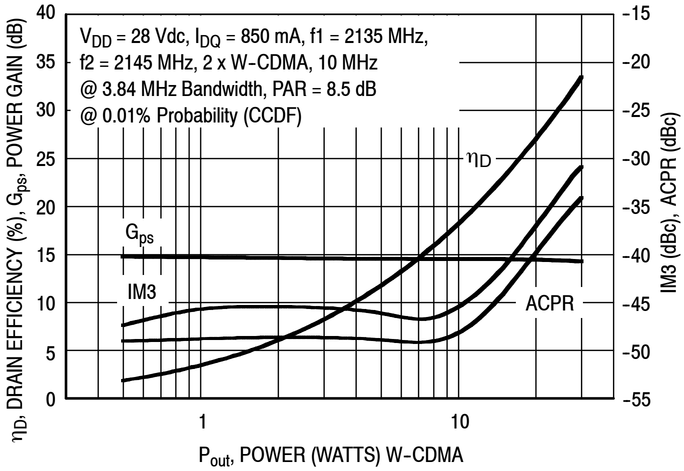
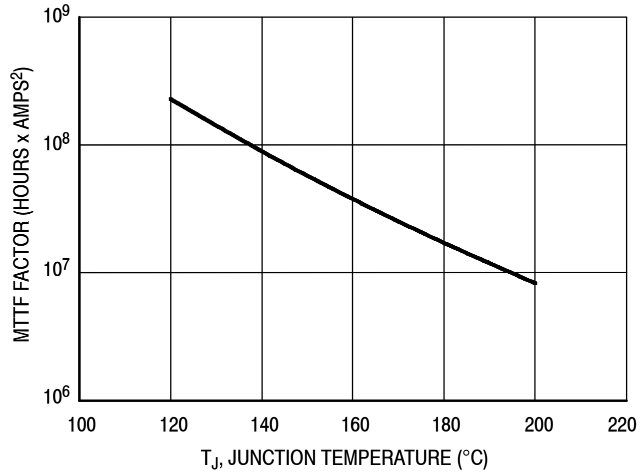


Figure 8. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power



This above graph displays calculated MTTF in hours x ampere^2 drain current. Life tests at elevated temperatures have correlated to better than ±10% of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 9. MTTF Factor versus Junction Temperature

W-CDMA TEST SIGNAL

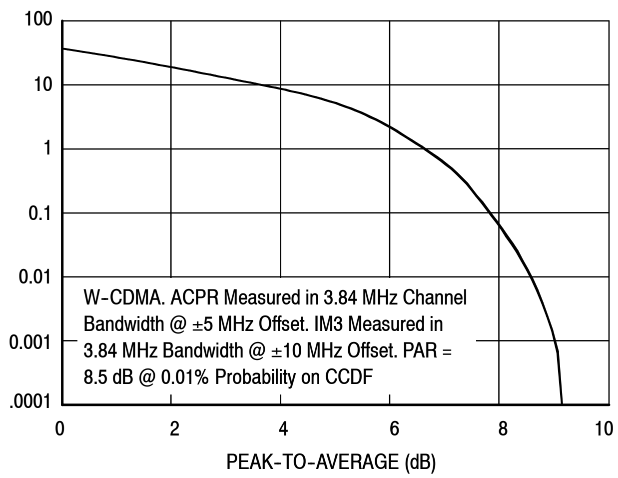


Figure 10. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single Carrier Test Signal

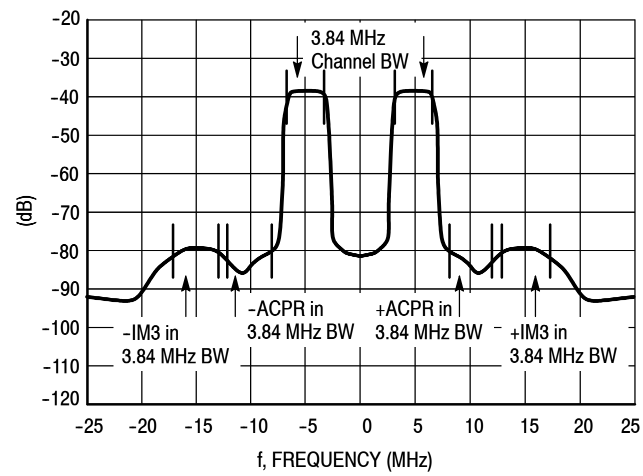
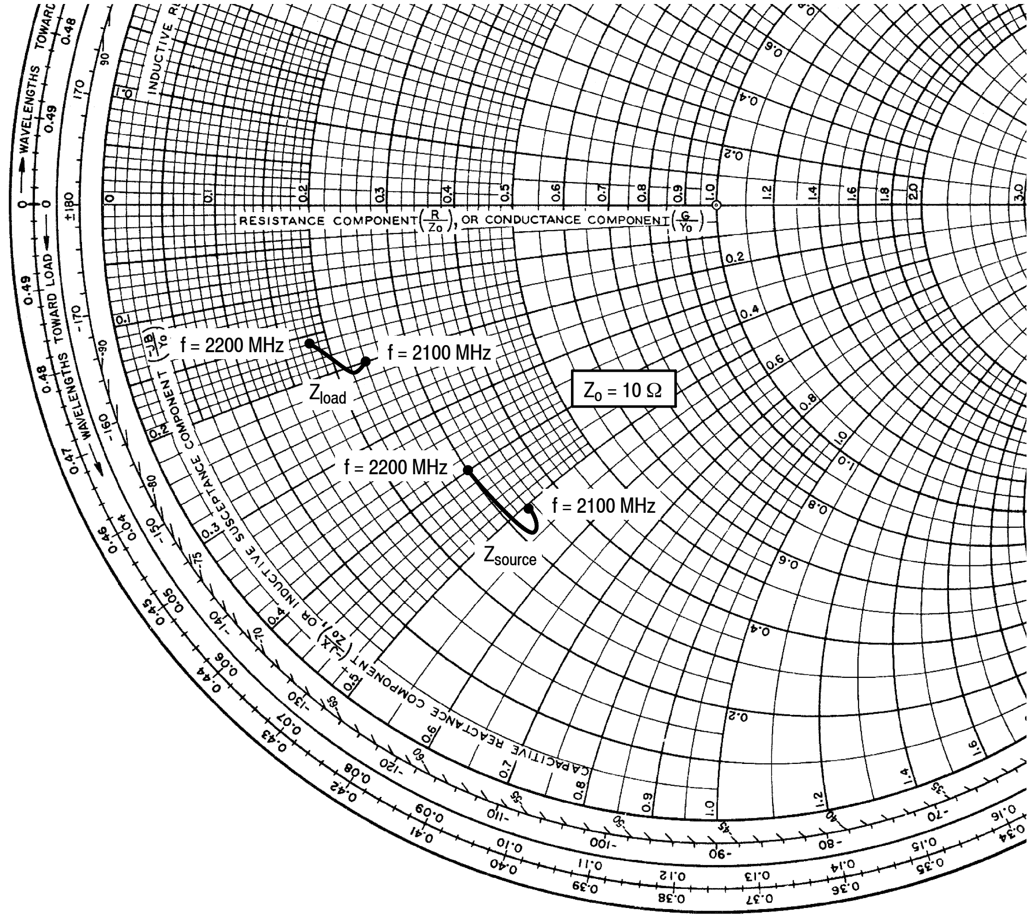


Figure 11. 2-Carrier W-CDMA Spectrum



V_{DD} = 28 Vdc, I_{DQ} = 850 mA, P_{out} = 19 W Avg.

f MHz	Z_{source} Ω	Z_{load} Ω
2100	3.4 - j5.1	2.4 - j2.0
2120	3.2 - j5.4	2.2 - j2.1
2160	3.0 - j4.4	2.1 - j1.9
2200	3.0 - j4.0	1.8 - j1.6

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

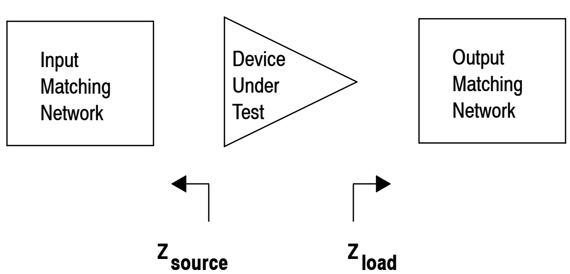
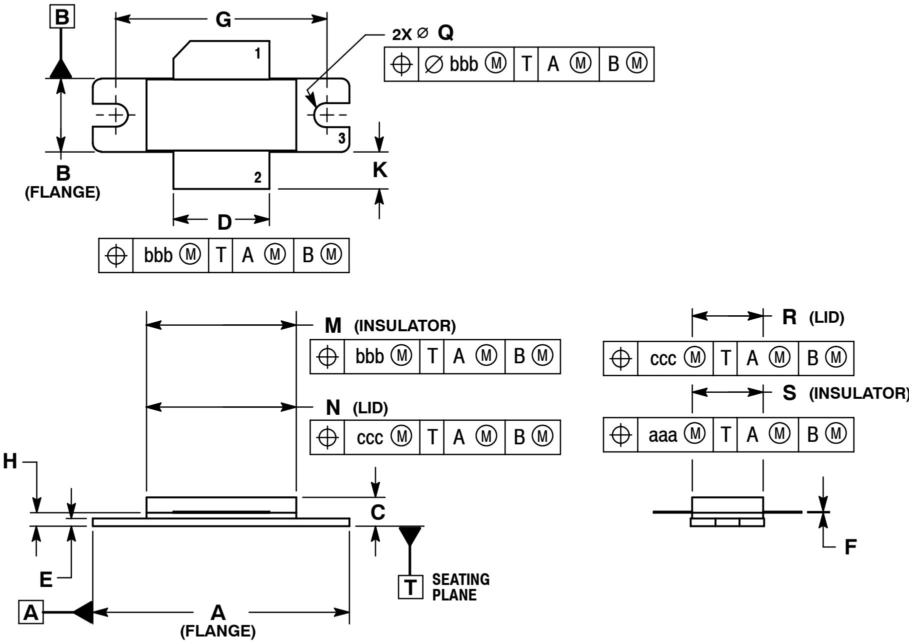


Figure 12. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS

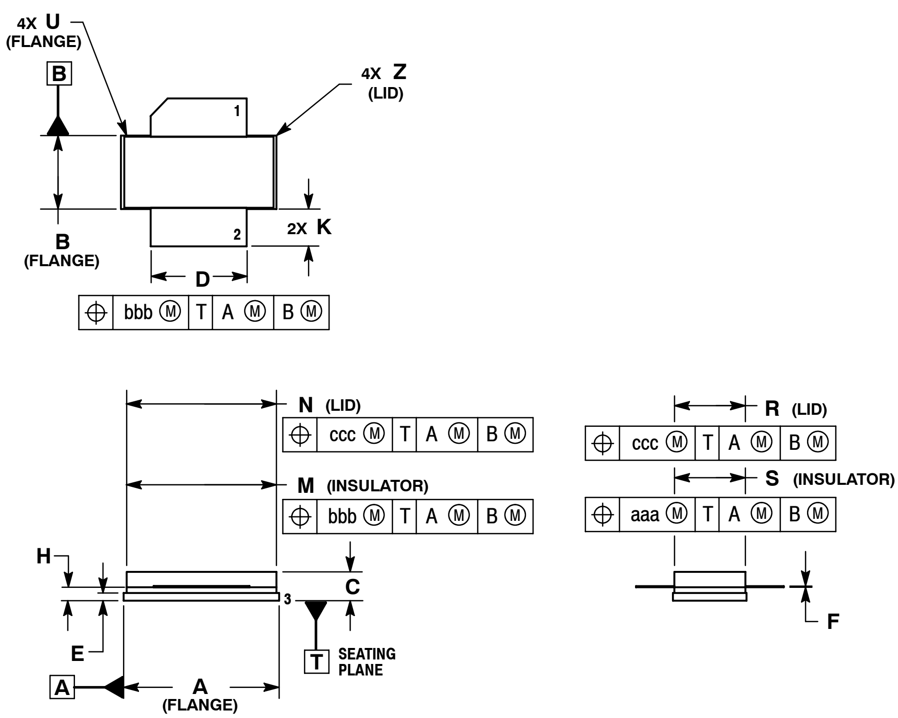


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	Ø.118	Ø.138	Ø3.00	Ø3.51
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 465-06
ISSUE G
NI-780
MRF5S21090HR3



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DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
5. SOURCE

CASE 465A-06
ISSUE H
NI-780S
MRF5S21090HSR3

ARCHIVE INFORMATION

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
3	Oct. 2008	• Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN12779, p. 1, 2 • Updated Part Numbers in Table 5, Component Designations and Values, to RoHS compliant part numbers, p. 3 • Added Product Documentation and Revision History, p. 9
	Dec. 2010	• Data sheet archived. Parts no longer manufactured.

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Technical Information Center, EL516
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Tempe, Arizona 85284
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Europe, Middle East, and Africa:
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Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
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+49 89 92103 559 (German)
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Japan:
Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor China Ltd.
Exchange Building 23F
No. 118 Jianguo Road
Chaoyang District
Beijing 100022
China
+86 10 5879 8000
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